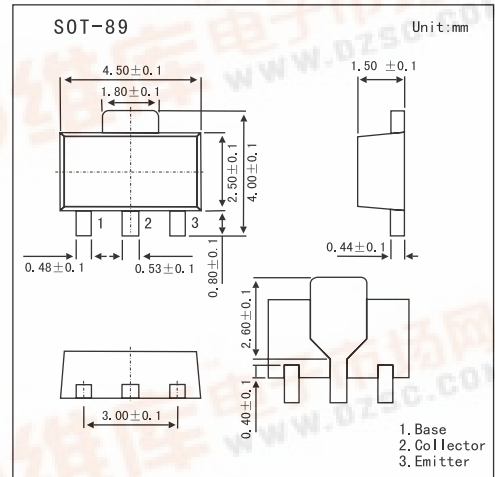


SMD Type Transistors

Silicon NPN Epitaxial Planar Type  
2SC5026

Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$ .
- High collector-emitter voltage (Base open)  $V_{CEO}$ .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	80	V
Collector-emitter voltage	$V_{CEO}$	80	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	1	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	$V_{CB0}$	$I_C = 10 \mu\text{A}, I_E = 0$	80			V
Collector-emitter voltage	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	80			V
Emitter-base voltage	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current	$I_{CBO}$	$V_{CB} = 40 \text{ V}, I_B = 0$			0.1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 2 \text{ V}, I_C = 100 \text{ mA}$	120		340	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.15	0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.2	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		10	20	pF

hFE Classification

Marking	2A	
Rank	R	S
$h_{FE}$	120~240	170~340

